

isc Silicon NPN Power Transistor

2SC5480

DESCRIPTION

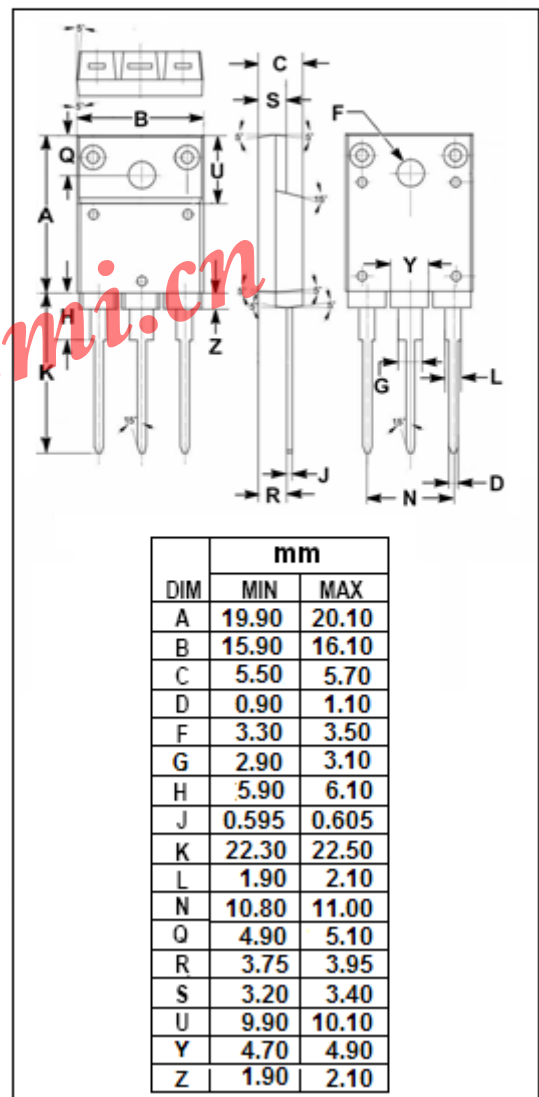
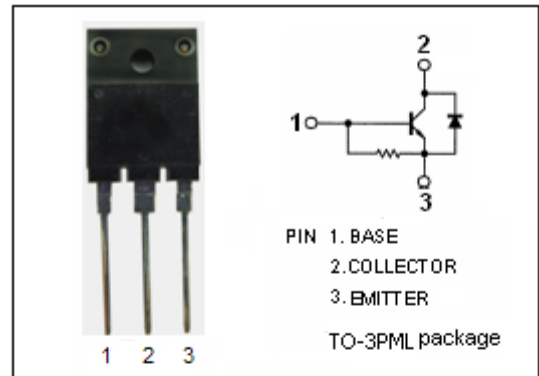
- High Breakdown Voltage-
: $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- Built-in Damper Diode

APPLICATIONS

- Designed for horizontal deflection output stage applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	5	V
$I_{C(peak)}$	Collector Current-Peak	14	A
$I_{C(surge)}$	Collector Current-Surge	28	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	50	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 500mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 2.5A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10A; I _B = 2.5A			1.5	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1500V; R _{BE} = 0			500	μ A
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	5		25	
h _{FE-2}	DC Current Gain	I _C = 10A; V _{CE} = 5V	4		7	
t _f	Fall Time	I _{CP} = 7A; I _{B1} = 2.4A; f _H = 31.5kHz			0.4	μ s

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